



BAS70x

DIODE

SCHOTTKY BARRIER DIODES

DESCRIPTION

Planar Schottky barrier diodes encapsulated in the SOT-23 small plastic SMD package. Single diodes and dual diodes with different pin configuration are available.

FEATURES

- * Low Turn-on voltage
- * Fast switching
- * Ultra-small surface mount package
- * Also available in lead free version

ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
BAS70G-AE2-R	SOT-23-3	x	A	K	Tape Reel
BAS70AG-AE2-R	SOT-23-3	K1	K2	A2A1	Tape Reel
BAS70CG-AE2-R	SOT-23-3	A1	A2	K2K1	Tape Reel
BAS70SG-AE2-R	SOT-23-3	K1	A2	K2A1	Tape Reel
BAS70G-AE3-R	SOT-23	x	A	K	Tape Reel
BAS70AG-AE3-R	SOT-23	K1	K2	A2A1	Tape Reel
BAS70CG-AE3-R	SOT-23	A1	A2	K2K1	Tape Reel
BAS70SG-AE3-R	SOT-23	K1	A2	K2A1	Tape Reel

Note: Pin Assignment: A: Anode K: Cathode x:NC

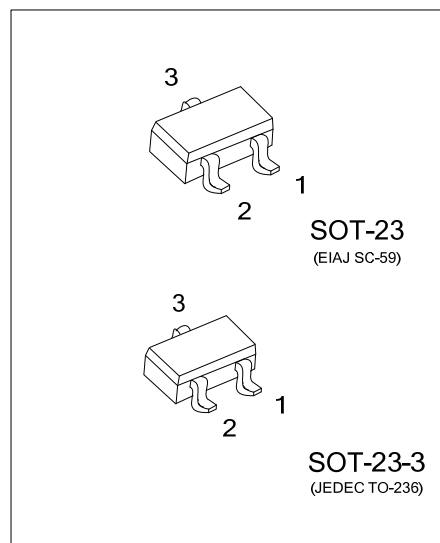
 BAS70xG-AE2-R	(1) Packing Type (2) Package Type (3) Green Package (4) Diode Configuration	(1) R: Tape Reel (2) AE2: SOT-23-3, AE3: SOT-23 (3) G: Halogen Free and Lead Free (4) x: refer to DIODE CONFIGURATION AND SYMBOL
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DIODE CONFIGURATION AND SYMBOL

BAS70	BAS70A	BAS70C	BAS70S

MARKING

BAS70	BAS70A	BAS70C	BAS70S



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNITS
DC Voltage	V_R	70	V
Forward Continuous Current	I_F	70	mA
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	-55 ~ +150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

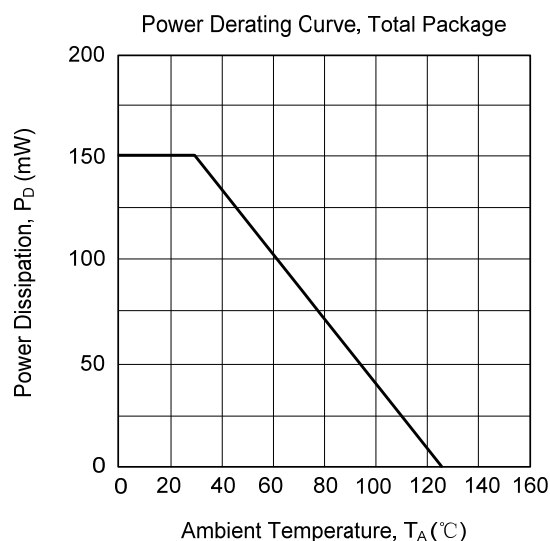
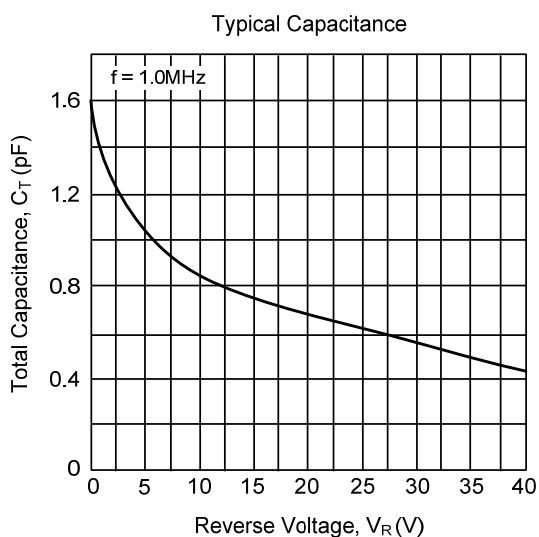
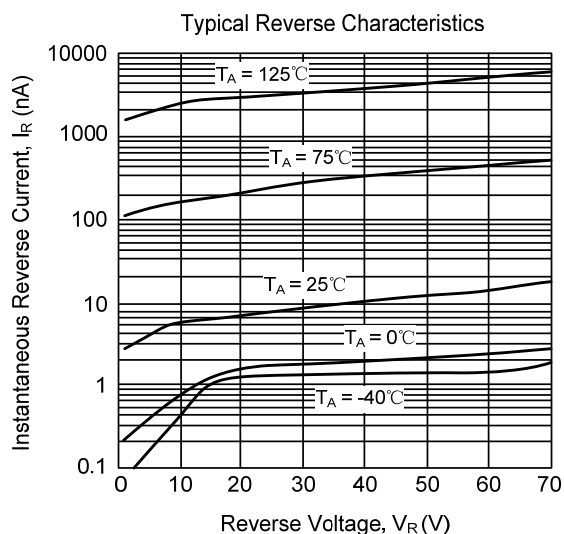
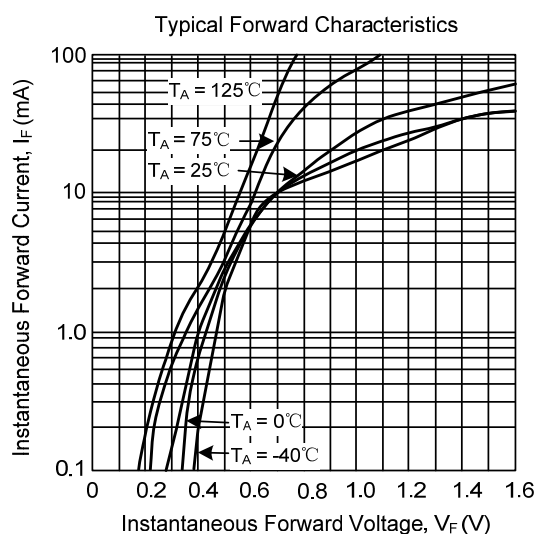
Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage	BV_R	$I_R=10\mu\text{A}$	70			V
Reverse Voltage Leakage Current	I_R	$V_R=50\text{V}$			100	nA
Forward Voltage	V_F	$I_F=1\text{mA}$			410	mV
		$I_F=15\text{mA}$			1000	mV
Diode Capacitance	C_D	$V_R=0\text{V}$, $f=1\text{MHz}$			2	pF
Reveres Recovery Time	t_{RR}	$I_F=I_R=10\text{mA}$, $I_{RR}=0.1 \times I_R$, $R_L=100\Omega$			5	nS

■ TYPICAL CHARACTERISTICS



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